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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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TBB1002

Twin Build in Biasing Circuit MOS FET IC VHF/UHF RF Amplifier

RENESAS

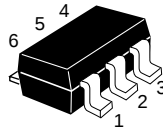
ADE-208-987F (Z)
7th. Edition
Dec. 2000

Features

- Small SMD package CMPAK-6 built in twin BBFET; To reduce using parts cost & PC board space.
- Suitable for World Standard Tuner RF amplifier.
- Very useful for total tuner cost reduction.
- Withstanding to ESD; Build in ESD absorbing diode. Withstand up to 200 V at C = 200 pF, Rs = 0 conditions.
- Provide mini mold packages; CMPAK-6

Outline

CMPAK-6



1. Gate-1(1)
2. Source
3. Drain(1)
4. Drain(2)
5. Gate-2
6. Gate-1(2)

- Notes:
1. Marking is "BM".
 2. TBB1002 is individual type number of HITACHI TWIN BBFET.

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	6	V
Gate1 to source voltage	V_{G1S}	+6 -0	V
Gate2 to source voltage	V_{G2S}	+6 -0	V
Drain current	I_D	30	mA
Channel power dissipation	P_{ch}^{*3}	250	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 3. Value on the glass epoxy board (49mm × 38mm × 1mm).

Electrical Characteristics (Ta = 25°C)

The below specification are applicable for UHF unit (FET1)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200\mu A$, $V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10\mu A$, $V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	+6	—	—	V	$I_{G2} = +10\mu A$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5V$, $V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I_{G2SS}	—	—	+100	nA	$V_{G2S} = +5V$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5V$, $V_{G2S} = 4V$, $I_D = 100\mu A$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5V$, $V_{G1S} = 5V$, $I_D = 100\mu A$
Drain current	$I_{D(op)}$	13	17	21	mA	$V_{DS} = 5V$, $V_{G1} = 5V$ $V_{G2S} = 4V$, $R_G = 100k\Omega$
Forward transfer admittance	$ y_{fs} $	21	26	31	mS	$V_{DS} = 5V$, $V_{G1} = 5V$, $V_{G2S} = 4V$ $R_G = 100k\Omega$, $f = 1kHz$
Input capacitance	C_{iss}	1.4	1.8	2.2	pF	$V_{DS} = 5V$, $V_{G1} = 5V$
Output capacitance	C_{oss}	1.0	1.4	1.8	pF	$V_{G2S} = 4V$, $R_G = 100k\Omega$
Reverse transfer capacitance	C_{rss}	—	0.02	0.04	pF	$f = 1MHz$
Power gain	PG	16	21	—	dB	$V_{DS} = V_{G1} = 5V$, $V_{G2S} = 4V$ $R_G = 100k\Omega$, $f = 900MHz$ $Z_i = S11^*$, $Z_o = S22^* (:PG)$
Noise figure	NF	—	1.7	2.5	dB	$Z_i = S11_{opt} (:NF)$

Electrical Characteristics (Ta = 25°C)

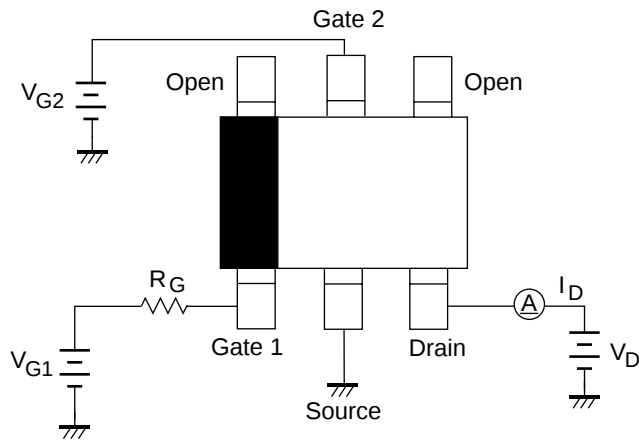
The below specification are applicable for VHF unit (FET2)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200\mu A$, $V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10\mu A$, $V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	+6	—	—	V	$I_{G2} = +10\mu A$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5V$, $V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I_{G2SS}	—	—	+100	nA	$V_{G2S} = +5V$, $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5V$, $V_{G2S} = 4V$, $I_D = 100\mu A$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.5	0.75	1.0	V	$V_{DS} = 5V$, $V_{G1S} = 5V$, $I_D = 100\mu A$
Drain current	$I_{D(op)}$	14	18	22	mA	$V_{DS} = 5V$, $V_{G1} = 5V$, $V_{G2S} = 4V$, $R_G = 82k\Omega$
Forward transfer admittance	$ y_{fs} $	20	25	30	mS	$V_{DS} = 5V$, $V_{G1} = 5V$, $V_{G2S} = 4V$, $R_G = 82k\Omega$, $f = 1kHz$
Input capacitance	C_{iss}	2.2	2.6	3.0	pF	$V_{DS} = 5V$, $V_{G1} = 5V$
Output capacitance	C_{oss}	1.2	1.6	2.0	pF	$V_{G2S} = 4V$, $R_G = 82k\Omega$
Reverse transfer capacitance	C_{rss}	—	0.03	0.05	pF	$f = 1MHz$
Power gain	PG	22	27	—	dB	$V_{DS} = V_{G1} = 5V$, $V_{G2S} = 4V$
Noise figure	NF	—	1.2	1.7	dB	$R_G = 82k\Omega$, $f = 200MHz$

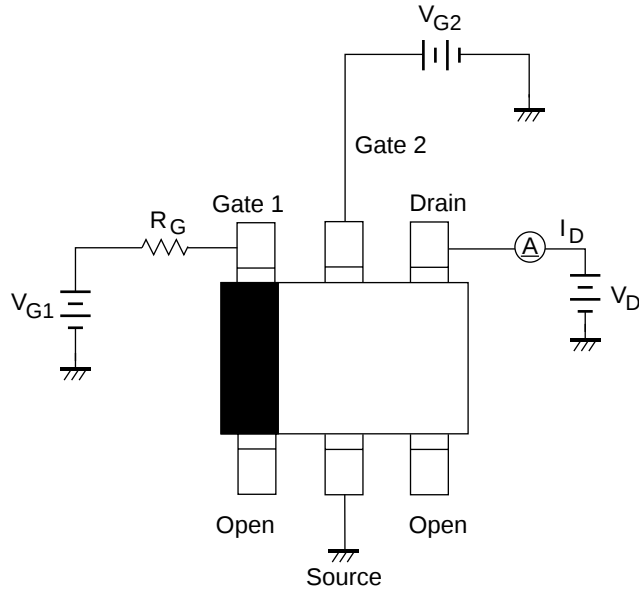
Test Circuits

- DC Biasing Circuit for Operating Characteristic Items ($I_{D(op)}$, $|y_{fs}|$, C_{iss} , C_{oss} , C_{rss} , NF , PG)

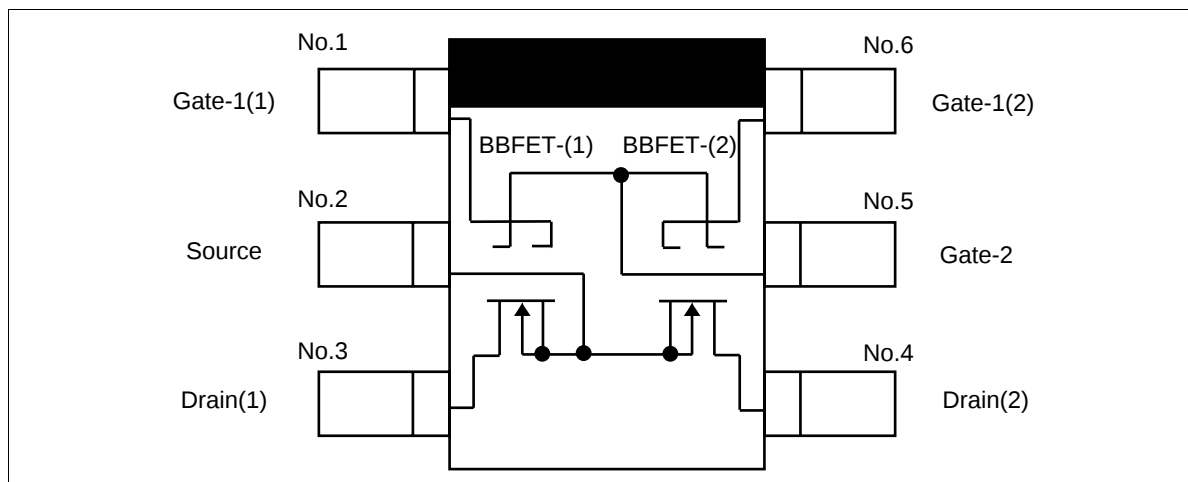
Measurment of FET1



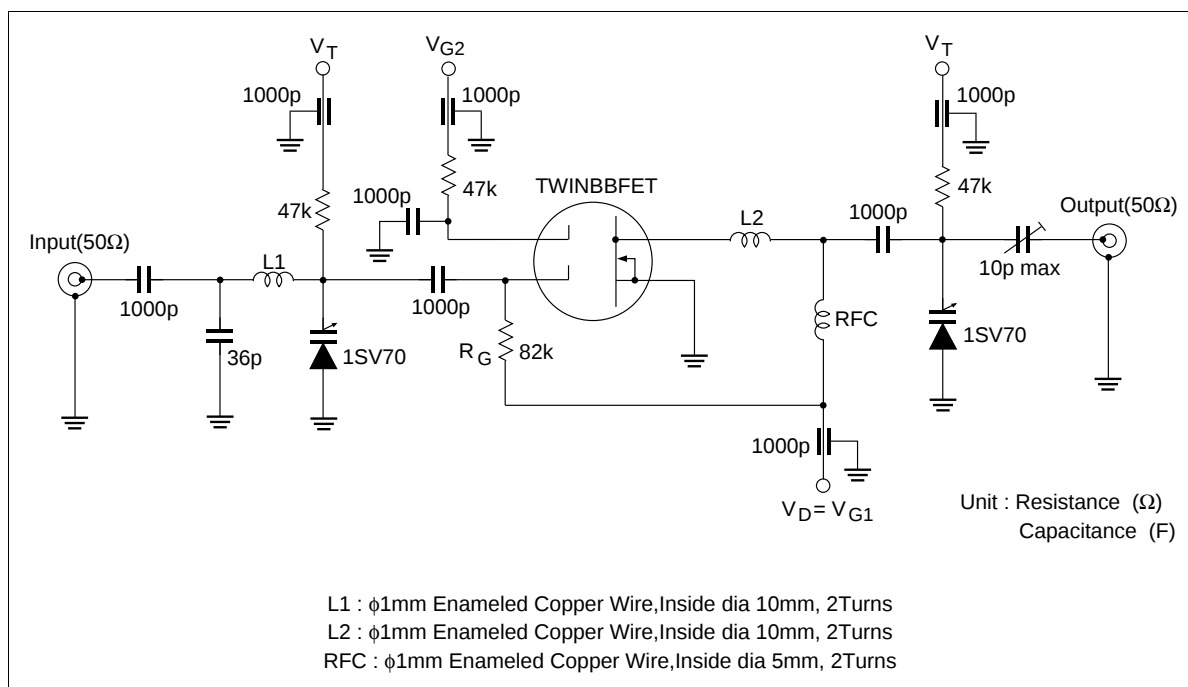
Measurment of FET2

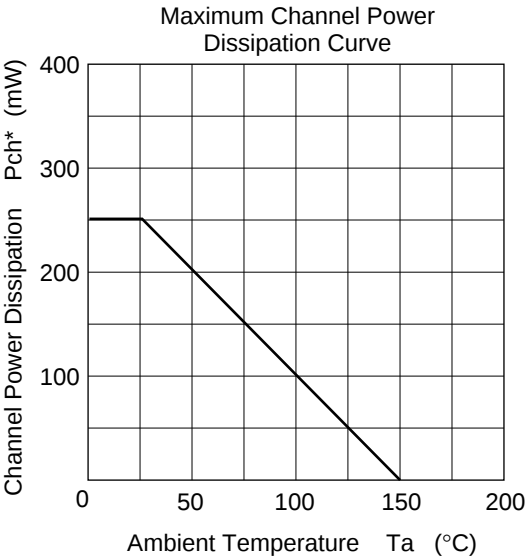


• Equivalent Circuit

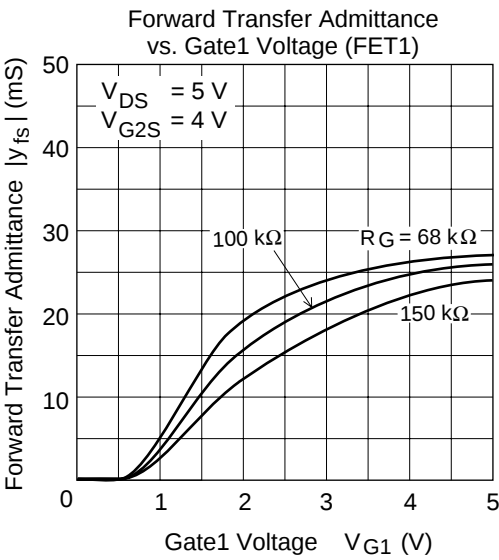
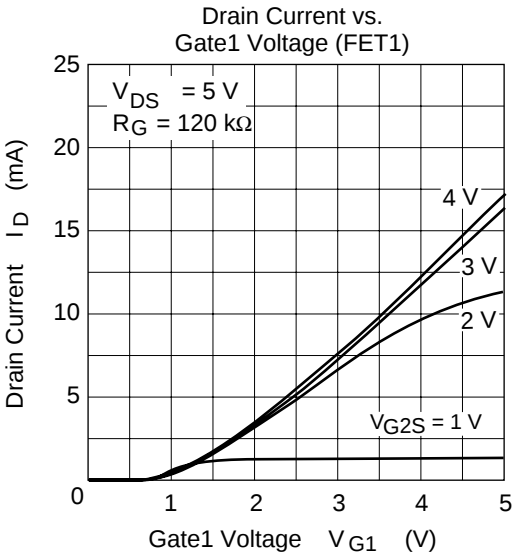
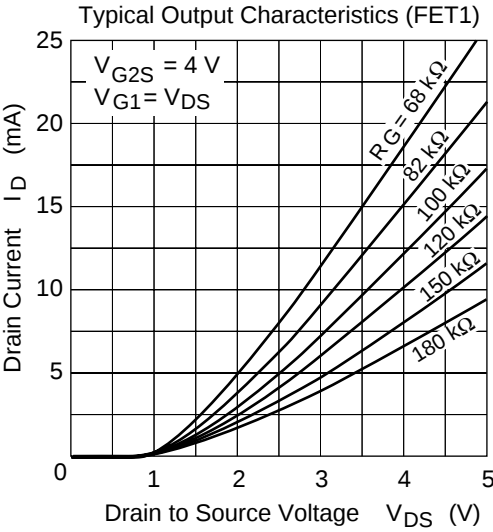


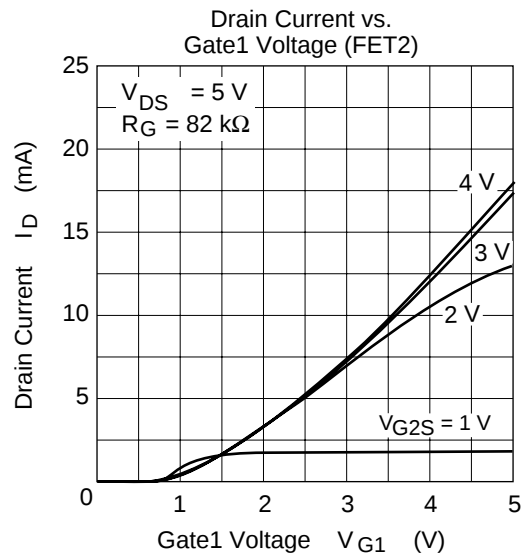
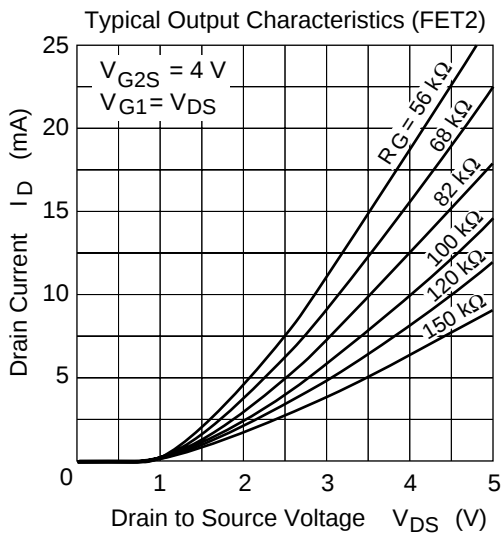
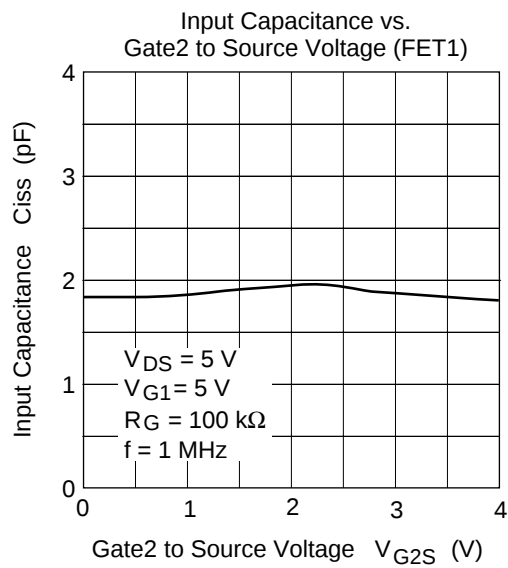
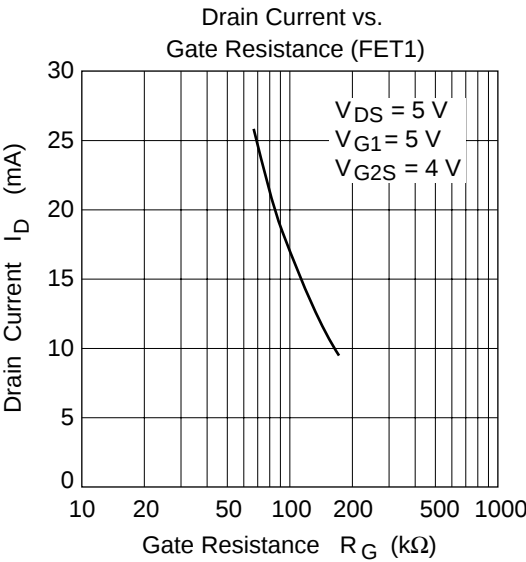
• 200 MHz Power Gain, Noise Figure Test Circuit

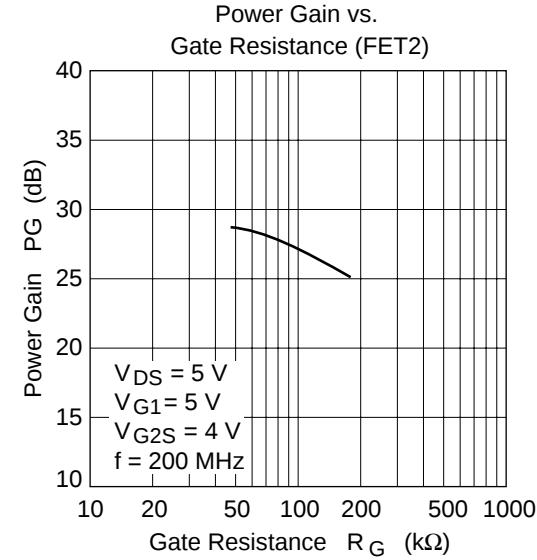
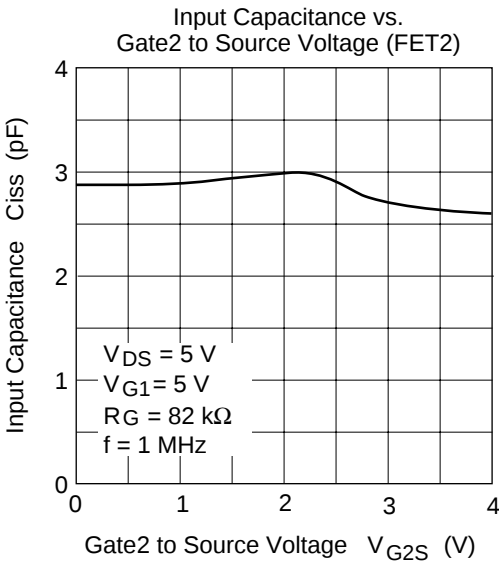
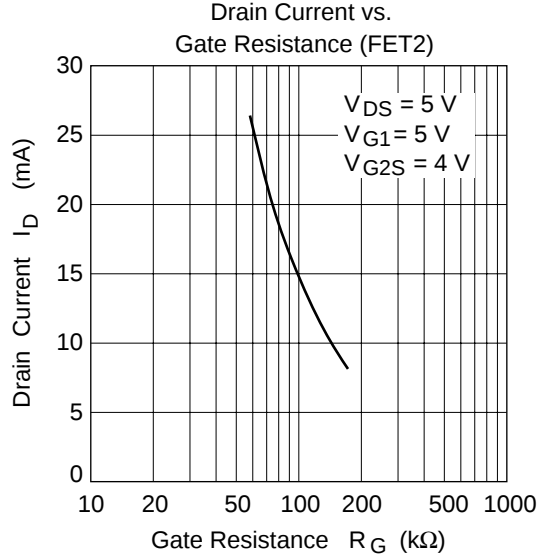
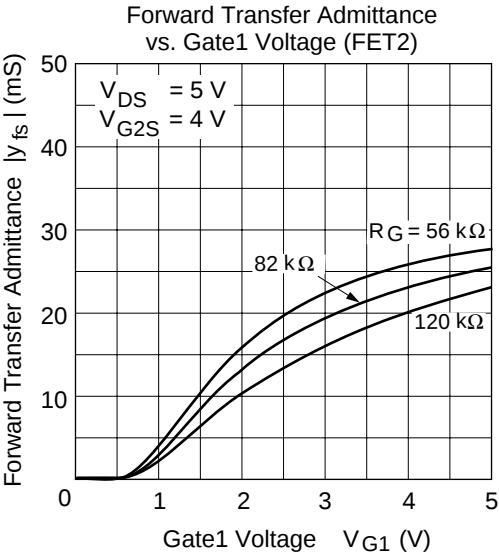


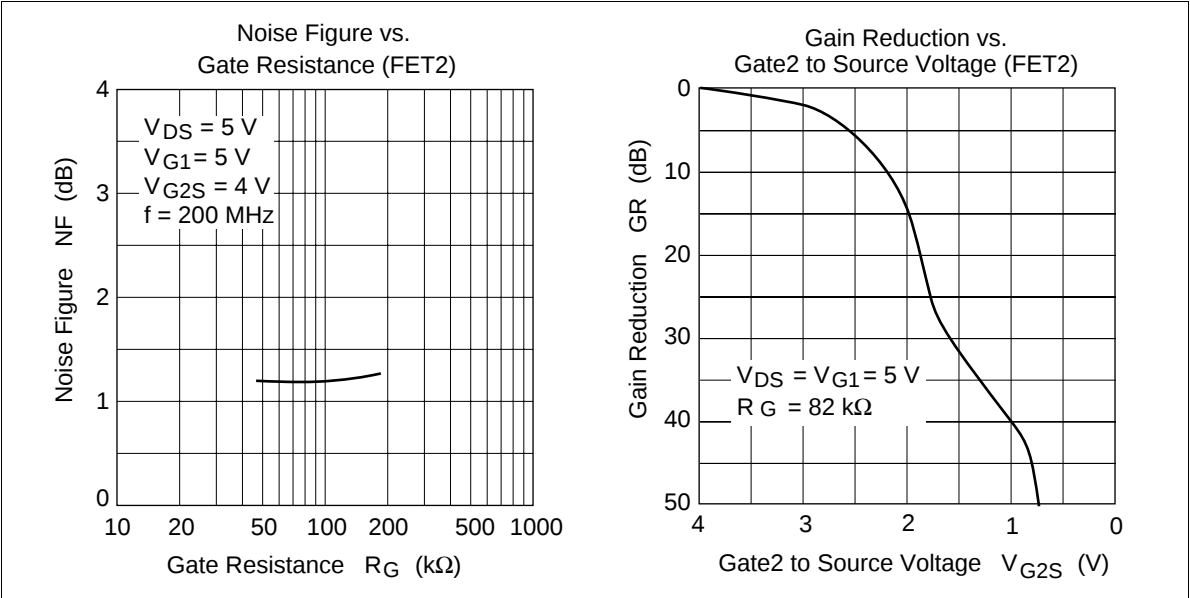


* Value on the glass epoxy board (49mm $\times$ 38mm $\times$ 1mm)



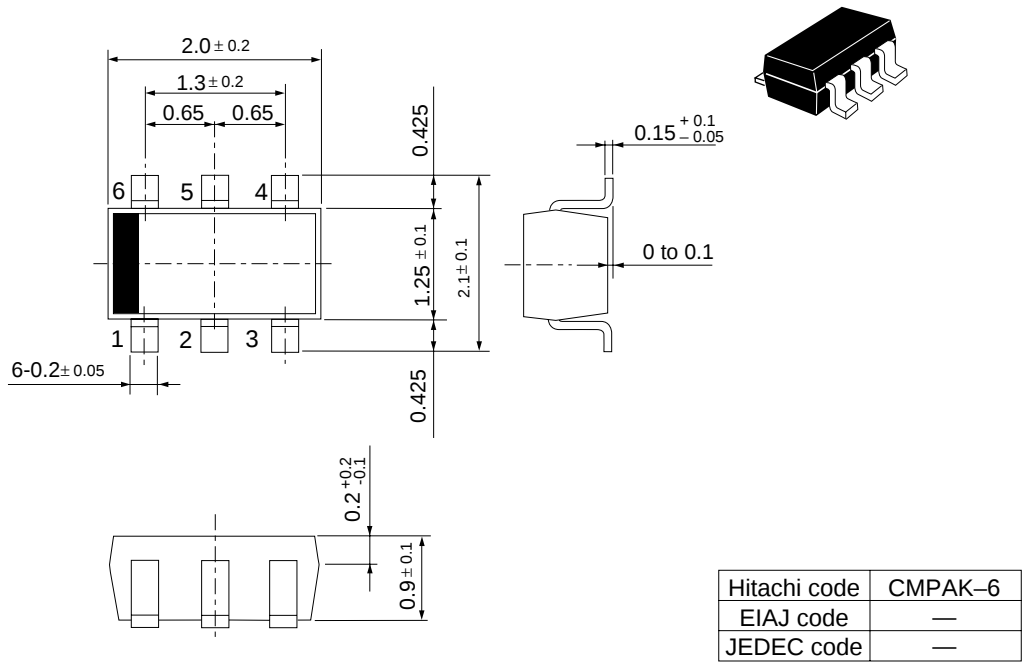






Package Dimensions

Unit: mm



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